

Listing of the Claims:

The following listing of the claims replaces all previous listings of the claims.

1-11. (Cancelled)

12. (Previously Presented) A method for fabricating finely patterned interconnects having low electrical resistance, the method comprising:

- (a) forming a finely patterned metal-containing interconnect having a first grain size on a carrier material; and
- (b) producing a locally delimited thermal region in the finely patterned metal-containing interconnect and moving the locally delimited thermal region in a direction of the interconnect in such a way that a recrystallization of the interconnect is carried out for the purpose of producing an interconnect having a second grain size, the second grain size being lengthened with respect to the first grain size in the direction of the movement.

13. (Previously Presented) The method of claim 12 wherein the finely patterned interconnect has feature sizes of less than 0.2 μm .

14. (Currently Amended) The method of claim 12 wherein,
in act (a), the interconnect is formed in a primary direction and/or in a secondary direction which is substantially perpendicular to the primary direction; and
in act (b), the movement of the thermal region is carried out substantially in the primary direction and/or in the secondary direction or at an angle of 45 degrees to the primary direction and the secondary ~~second~~ direction.

15. (Previously Presented) The method of claim 12 wherein act (b) is carried out repeatedly.

16. (Previously Presented) The method of claim 12 wherein, in act (b), the locally delimited thermal region is produced by means of a fanned-out laser beam, a hot gas, a multiplicity of heating lamps and/or a heating wire.
17. (Previously Presented) The method of claim 12 wherein the locally delimited thermal region is formed in strip-type or point-type fashion.
18. (Currently Amended) The method of claim 12 wherein, in act (a), the interconnect has a metal alloy or a doped metal with an impurity proportion of less than 5% of atoms or 5at%, by weight.
19. (Previously Presented) The method of claim 12 wherein the carrier material has a diffusion barrier layer and/or a seed layer.
20. (Previously Presented) The method of claim 12 wherein, in act (a), a damascene method is carried out.
21. (Previously Presented) The method of claim 12, wherein the locally delimited thermal region has a temperature of 150 degrees Celsius to 450 degrees Celsius.
22. (Previously Presented) The method of claim 12 wherein the recrystallization is carried out in a protective gas atmosphere.
23. (Currently Amended) A method for fabricating finely patterned interconnects having low electrical resistance, the method comprising:
- (a) forming a finely patterned metal-containing interconnect having a first grain size on a carrier material; and
 - (b) producing a locally delimited thermal region in the finely patterned metal-containing interconnect and moving the locally delimited thermal region in a direction of the interconnect in such a way that a recrystallization of the interconnect is carried out for the purpose of producing an interconnect

having a second grain size, the second grain size being lengthened
~~enlarged~~ with respect to the first grain size in the direction of the
movement;

wherein the finely patterned interconnect has feature sizes ~~features-size~~ of less
than 0.2 μ m, ~~0.2 μ m~~;

24. (Cancelled).

25. (Currently Amended) A method for fabricating finely patterned interconnects
having low electrical resistance, the method comprising:

- (a) forming a finely patterned metal-containing interconnect having a first
grain size on a carrier material; and
- (b) producing a locally delimited thermal region in the finely patterned metal-
containing interconnect and moving the locally delimited thermal region in
a direction of the interconnect at approximately 1 cm/second in such a
way that a recrystallization of the interconnect is carried out for the
purpose of producing an interconnect having a second grain size, the
second grain size being lengthened ~~enlarged~~ with respect to the first grain
size in the direction of the movement.

26. (Cancelled)